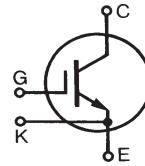


# GenX3™ 600V IGBT

# IXGN200N60B3

Medium-Speed Low-V<sub>sat</sub> PT IGBT for 5-40kHz Switching

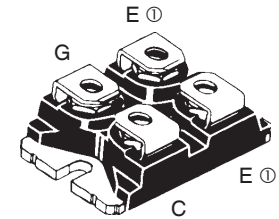


$$V_{CES} = 600V$$

$$I_{C110} = 200A$$

$$V_{CE(sat)} \leq 1.50V$$

SOT-227B, miniBLOC  
 E153432



G = Gate, C = Collector, E = Emitter  
 ① Either Emitter Terminal can be used as Main or Kelvin Emitter

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	600	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	300	A
$I_{C110}$	$T_C = 110^\circ C$	200	A
$I_{LRMS}$	Terminal Current Limit	200	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	1200	A
<b>SSOA</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 1\Omega$	$I_{CM} = 300$	A
<b>(RBSOA)</b>	Clamped Inductive Load	$V_{CE} \leq V_{CES}$	
$P_C$	$T_C = 25^\circ C$	830	W
$T_J$		- 55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		- 55 ... +150	$^\circ C$
$V_{ISOL}$	50/60Hz	$t = 1min$	2500 V~
	$I_{ISOL} \leq 1mA$	$t = 1s$	3000 V~
$M_d$	Mounting Torque	1.5/13	Nm/lb.in.
	Terminal Connection Torque (M4)	1.3/11.5	Nm/lb.in.
<b>Weight</b>		30	g

## Features

- International Standard Package miniBLOC
- UL Recognized
- Aluminium Nitride Isolation
  - High Power Dissipation
- Isolation Voltage 3000 V~
- Very High Current IGBT
- Low  $V_{CE(sat)}$  for Minimum on-state Conduction Losses
- MOS Gate Turn-On
  - Drive Simplicity
- Low Collector-to-Case Capacitance (< 50 pF)
- Low Package Inductance (< 5 nH)
  - Easy to Drive and to Protect

## Advantages

- High Power Density
- Low Gate Drive Requirement

## Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- DC Choppers
- AC Motor Speed Drives
- DC Servo and Robot Drives

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 5 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 100A$ , $V_{GE} = 15V$ , Note 1 $I_C = 200A$ , $T_J = 125^\circ C$	1.35	1.50	V
		1.65		V
		1.75		V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 60\text{A}, V_{CE} = 10\text{V}$ , Note 1	95	160	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		26	nF
$C_{oes}$			1260	pF
$C_{res}$			97	pF
$Q_{g(on)}$	$I_C = 100\text{V}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		750	nC
$Q_{ge}$			115	nC
$Q_{gc}$			245	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 300\text{V}, R_G = 1\Omega$		44	ns
$t_{ri}$			83	ns
$E_{on}$			1.6	mJ
$t_{d(off)}$			310	450 ns
$t_{fi}$			183	300 ns
$E_{off}$			2.9	4.5 mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 300\text{V}, R_G = 1\Omega$		42	ns
$t_{ri}$			80	ns
$E_{on}$			2.4	mJ
$t_{d(off)}$			430	ns
$t_{fi}$			300	ns
$E_{off}$			4.2	mJ
$R_{thJC}$				0.15 $^\circ\text{C/W}$
$R_{thCK}$		0.05		$^\circ\text{C/W}$

### SOT-227B miniBLOC



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

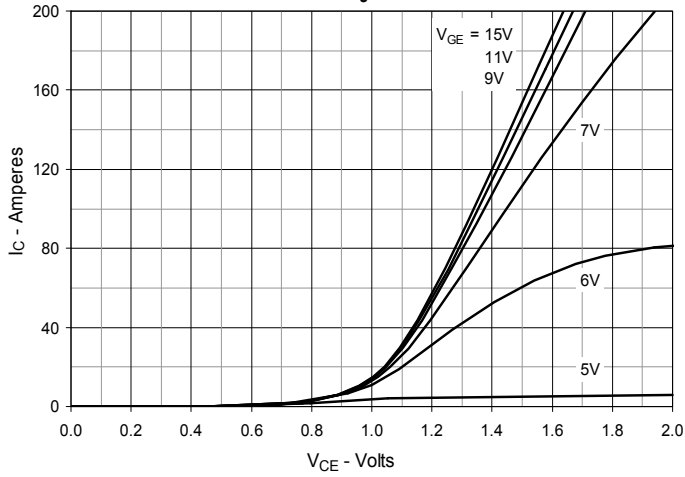
Note 1. Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

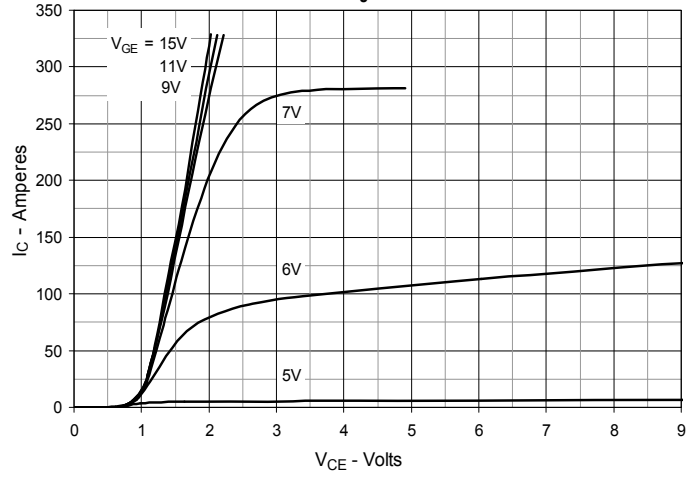
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

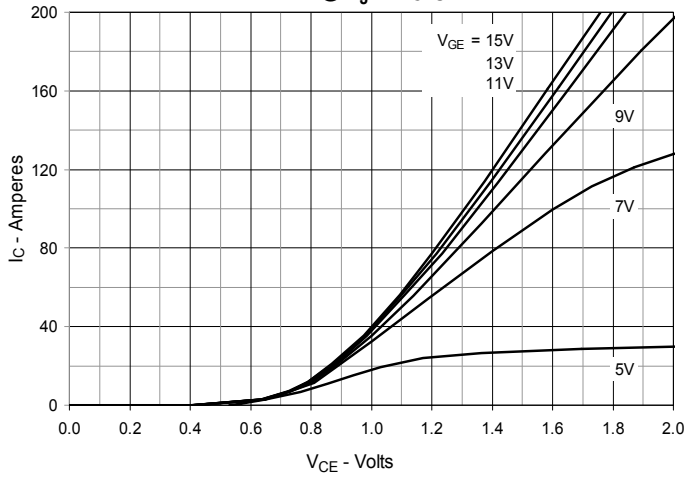
**Fig. 1. Output Characteristics**  
@  $T_J = 25^\circ\text{C}$



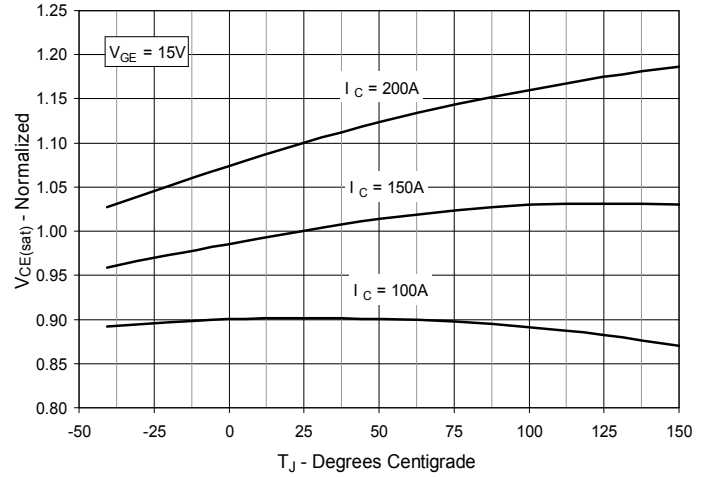
**Fig. 2. Extended Output Characteristics**  
@  $T_J = 25^\circ\text{C}$



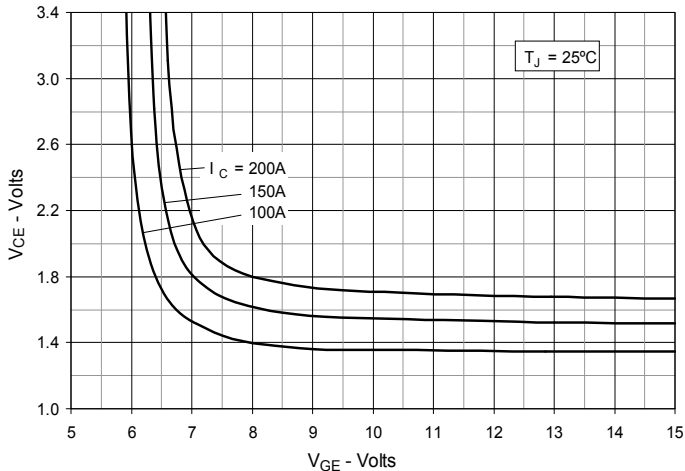
**Fig. 3. Output Characteristics**  
@  $T_J = 125^\circ\text{C}$



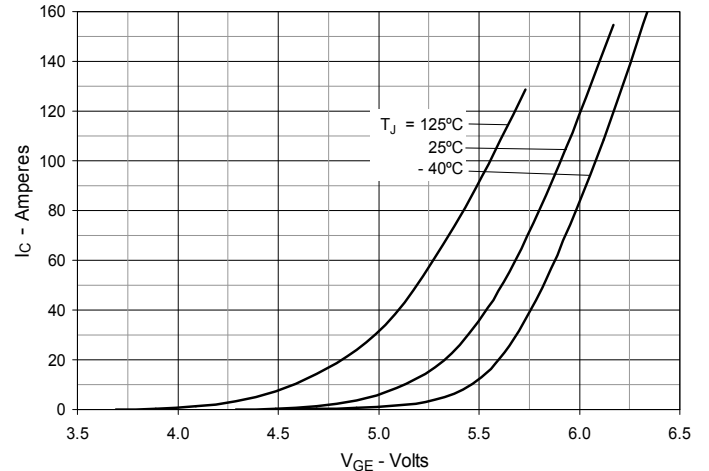
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



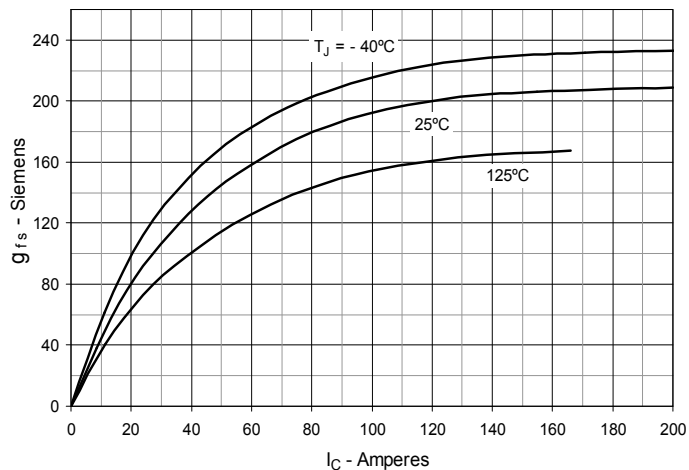
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



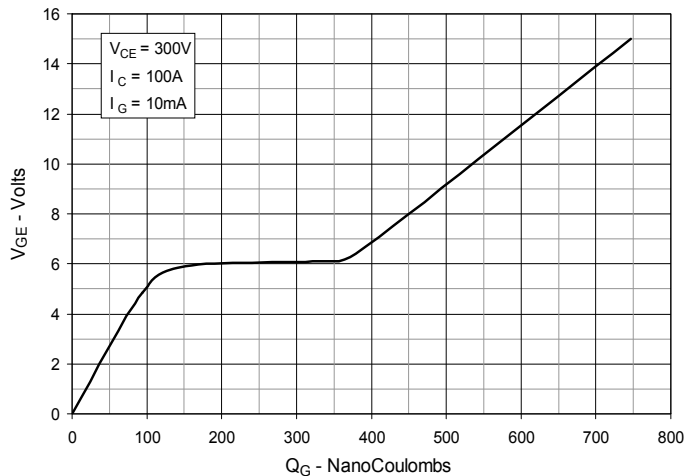
**Fig. 6. Input Admittance**



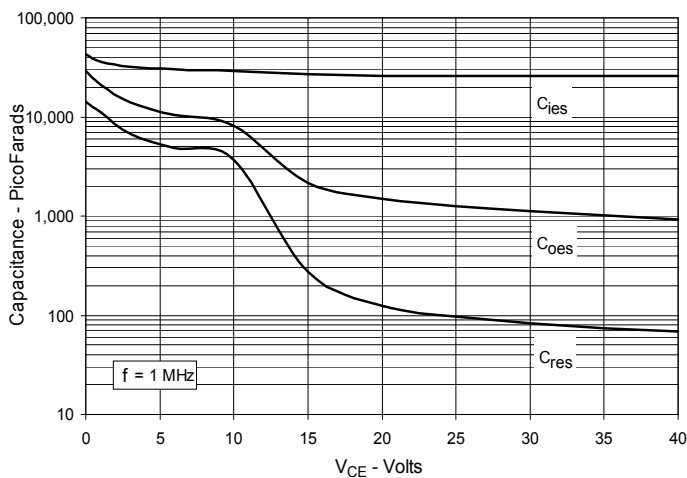
**Fig. 7. Transconductance**



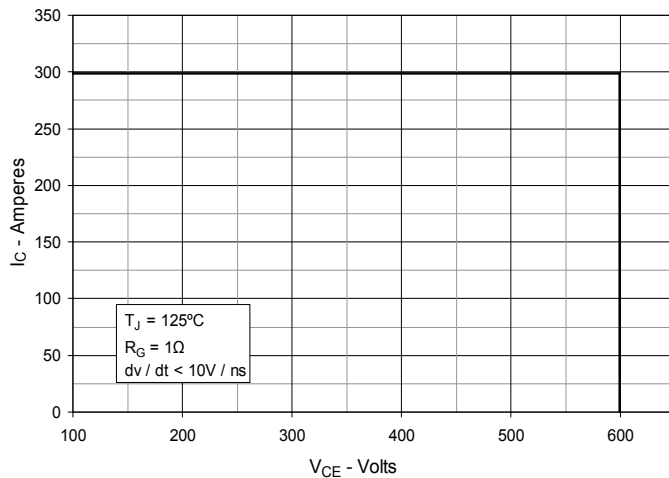
**Fig. 8. Gate Charge**



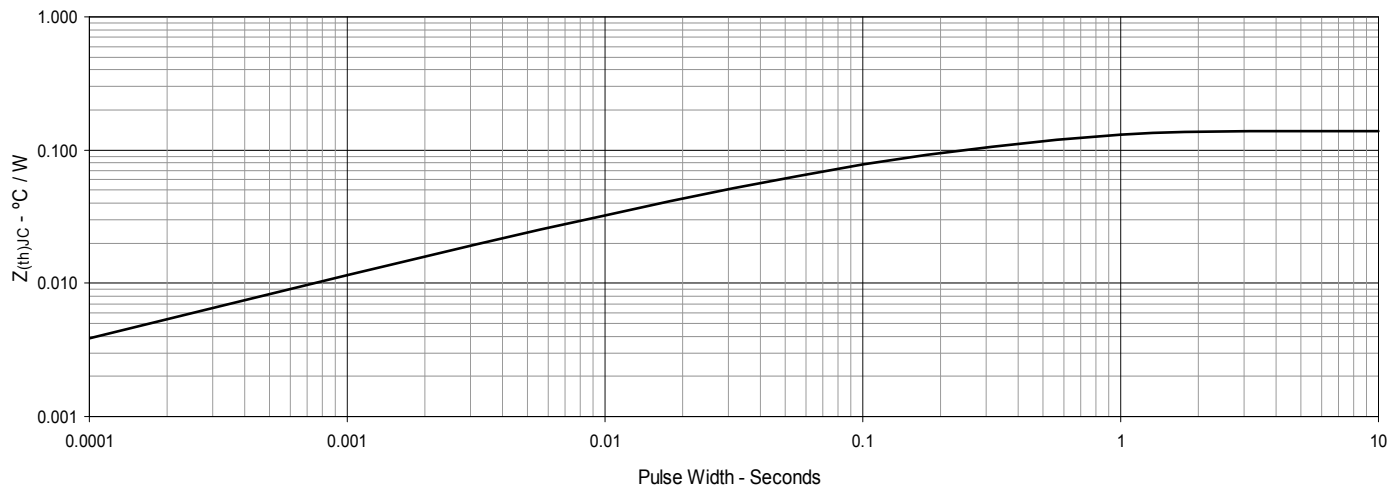
**Fig. 9. Capacitance**



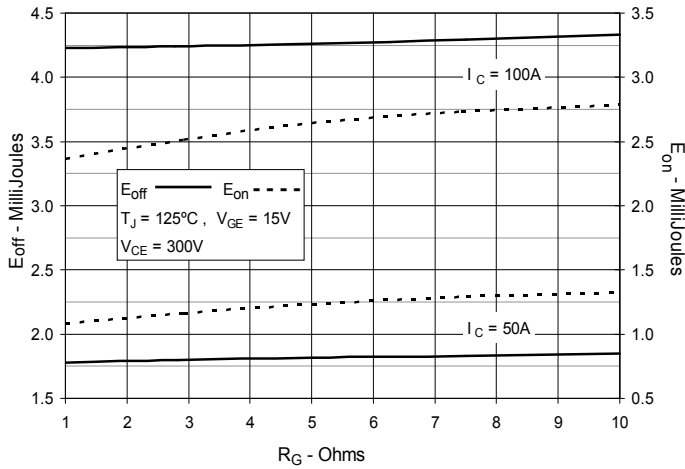
**Fig. 10. Reverse-Bias Safe Operating Area**



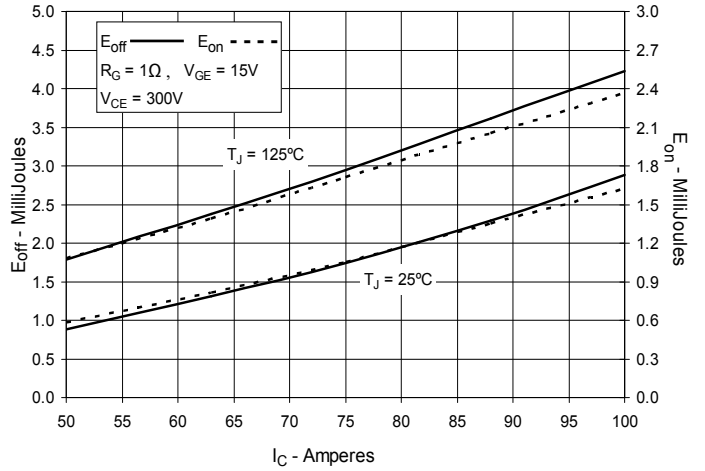
**Fig. 11. Maximum Transient Thermal Impedance**



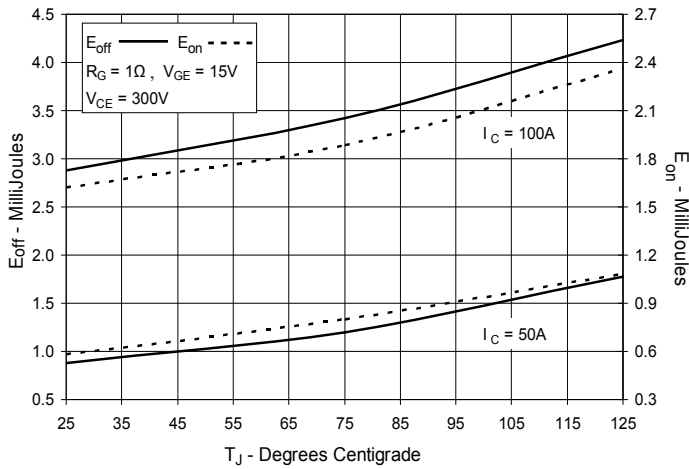
**Fig. 12. Inductive Switching  
Energy Loss vs. Gate Resistance**



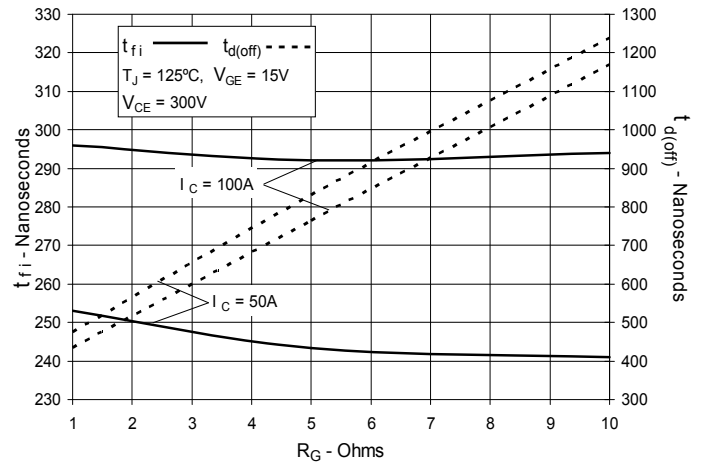
**Fig. 13. Inductive Switching  
Energy Loss vs. Collector Current**



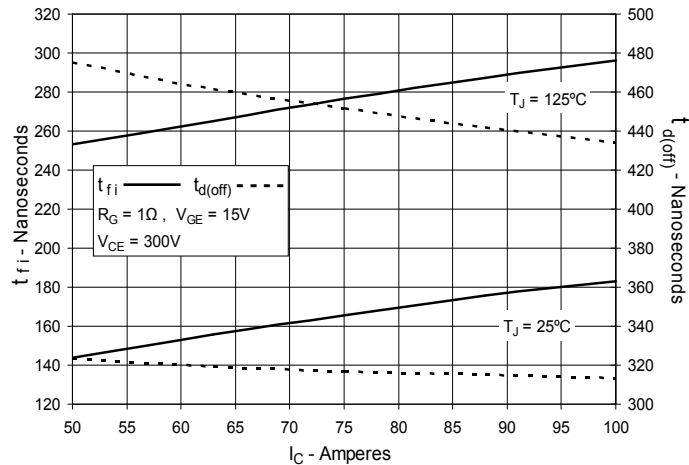
**Fig. 14. Inductive Switching  
Energy Loss vs. Junction Temperature**



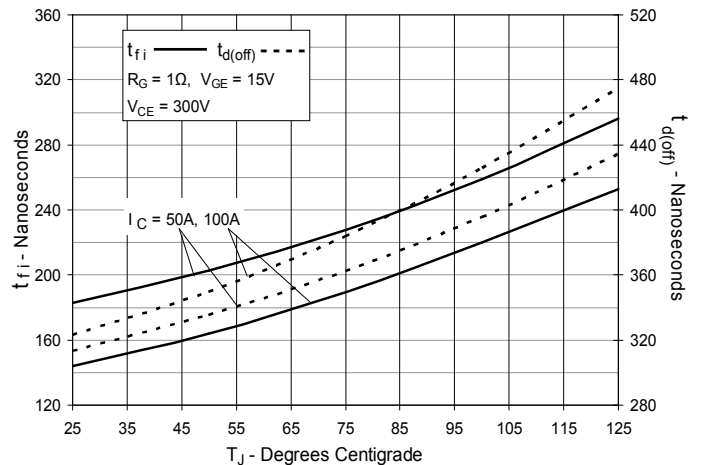
**Fig. 15. Inductive Turn-off  
Switching Times vs. Gate Resistance**



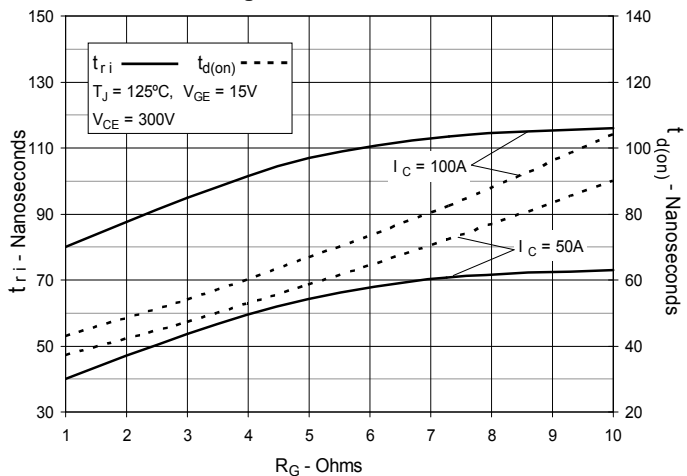
**Fig. 16. Inductive Turn-off  
Switching Times vs. Collector Current**



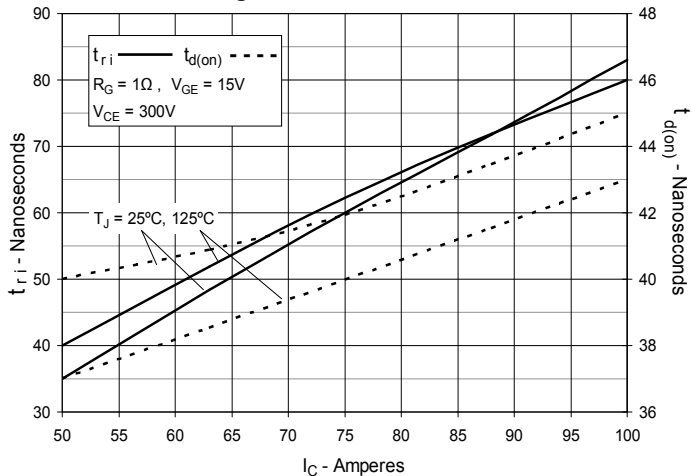
**Fig. 17. Inductive Turn-off  
Switching Times vs. Junction Temperature**



**Fig. 18. Inductive Turn-on  
Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on  
Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on  
Switching Times vs. Junction Temperature**

